

Bobo Tian

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

50
papers

965
citations

16
h-index

30
g-index

55
ext. papers

1,306
ext. citations

6
avg, IF

4.39
L-index

#	Paper	IF	Citations
50	Single-Crystalline Thin-Film Memory Arrays of Molecular Ferroelectrics with Ultralow Operation Voltages <i>2022</i> , 4, 758-763		1
49	Ferroelectric photosensor network: an advanced hardware solution to real-time machine vision.. <i>Nature Communications</i> , 2022 , 13, 1707	17.4	8
48	Molecular ferroelectric/semiconductor interfacial memristors for artificial synapses. <i>Npj Flexible Electronics</i> , 2022 , 6,	10.7	2
47	Ultralow-Power Machine Vision with Self-Powered Sensor Reservoir.. <i>Advanced Science</i> , 2022 , e2106092	13.6	8
46	Ferroelectric polymers for neuromorphic computing. <i>Applied Physics Reviews</i> , 2022 , 9, 021309	17.3	2
45	Amorphous ZrO ₂ Tunnel Junction Memristor With a Tunneling Electroresistance Ratio Above 400. <i>IEEE Electron Device Letters</i> , 2021 , 42, 696-699	4.4	0
44	Flexible Vertical Photogating Transistor Network with an Ultrashort Channel for In-Sensor Visual Nociceptor. <i>Advanced Functional Materials</i> , 2021 , 31, 2104327	15.6	25
43	Artificial Synapse Based on Organic-Inorganic Hybrid Perovskite with Electric and Optical Modulation. <i>Advanced Electronic Materials</i> , 2021 , 7, 2100291	6.4	10
42	Wafer-Scale Diisopropylammonium Bromide Films for Low-Power Lateral Organic Ferroelectric Capacitors. <i>Advanced Electronic Materials</i> , 2021 , 7, 2000778	6.4	3
41	Ferroelectric Synaptic Transistor Network for Associative Memory. <i>Advanced Electronic Materials</i> , 2021 , 7, 2001276	6.4	17
40	An air-stable artificial synapse based on a lead-free double perovskite Cs ₂ AgBiBr ₆ film for neuromorphic computing. <i>Journal of Materials Chemistry C</i> , 2021 , 9, 5706-5712	7.1	13
39	Research progress on solutions to the sneak path issue in memristor crossbar arrays. <i>Nanoscale Advances</i> , 2020 , 2, 1811-1827	5.1	55
38	Nonvolatile Negative Optoelectronic Memory Based on Ferroelectric Thin Films. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 1035-1040	4	9
37	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. <i>Nature Electronics</i> , 2020 , 3, 43-50	28.4	98
36	Preparation and multiferroicity of a novel two-dimensional material NiH ₂ SeO ₄ . <i>Journal of Materials Chemistry C</i> , 2020 , 8, 14812-14818	7.1	2
35	Self-assembled non-volatile micro memory arrays of molecular ferroelectrics. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 16742-16748	7.1	3
34	Graphene-ferroelectric transistors as complementary synapses for supervised learning in spiking neural network. <i>Npj 2D Materials and Applications</i> , 2019 , 3,	8.8	39

33	Two-Dimensional Ferroelectric Tunnel Junction: The Case of Monolayer In:SnSe/SnSe/Sb:SnSe Homostructure. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 1133-1140	4	34
32	Ferroelectric polarization-controlled resistive switching in BaTiO ₃ /SmNiO ₃ epitaxial heterostructures. <i>Applied Physics Letters</i> , 2019 , 114, 102901	3.4	11
31	Mediation in the second-order synaptic emulator with conductive atomic force microscopy. <i>Nanoscale</i> , 2019 , 11, 8744-8751	7.7	9
30	Ultra-wide temperature electronic synapses based on self-rectifying ferroelectric memristors. <i>Nanotechnology</i> , 2019 , 30, 464001	3.4	10
29	Efficient two-terminal artificial synapse based on a network of functionalized conducting polymer nanowires. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 9933-9938	7.1	18
28	Characterization and Application of PVDF and Its Copolymer Films Prepared by Spin-Coating and Langmuir-Blodgett Method. <i>Polymers</i> , 2019 , 11,	4.5	47
27	A Robust Artificial Synapse Based on Organic Ferroelectric Polymer. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800600	6.4	81
26	Ferroelectric Synapses: A Robust Artificial Synapse Based on Organic Ferroelectric Polymer (Adv. Electron. Mater. 1/2019). <i>Advanced Electronic Materials</i> , 2019 , 5, 1970006	6.4	0
25	Structural, electrical and magnetic properties of (110)-oriented BF-BZT-ST Films. <i>Ceramics International</i> , 2018 , 44, 9053-9057	5.1	2
24	Doping and band gap control at poly(vinylidene fluoride)/graphene interface. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 195303	3	3
23	Solid-State Synapse Based on Magnetoelectrically Coupled Memristor. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 5649-5656	9.5	41
22	Graphene Dirac point tuned by ferroelectric polarization field. <i>Nanotechnology</i> , 2018 , 29, 134002	3.4	9
21	A High-Speed and Low-Power Multistate Memory Based on Multiferroic Tunnel Junctions. <i>Advanced Electronic Materials</i> , 2018 , 4, 1700560	6.4	25
20	Ferroelectric FET for nonvolatile memory application with two-dimensional MoSe ₂ channels. <i>2D Materials</i> , 2017 , 4, 025036	5.9	63
19	Polarization switching in ultrathin polyvinylidene fluoride homopolymer ferroelectric films. <i>Ferroelectrics</i> , 2017 , 509, 143-157	0.6	13
18	Interfacial memristors in Al-LaNiO heterostructures. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 16960-16968	5.1	16
17	Preparation of La _{0.67} Ca _{0.23} Sr _{0.1} MnO ₃ thin films with interesting electrical and magnetic properties via pulsed-laser deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , 2017 , 60, 1	3.6	3
16	Transparent PVDF-TrFE/Graphene Oxide Ultrathin Films with Enhanced Energy Harvesting Performance. <i>ChemistrySelect</i> , 2017 , 2, 7951-7955	1.8	9

15	Electrical characterization of MoS ₂ field-effect transistors with different dielectric polymer gate. <i>AIP Advances</i> , 2017 , 7, 065121	1.5	7
14	Optoelectronic Properties of Few-Layer MoS FET Gated by Ferroelectric Relaxor Polymer. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 32083-32088	9.5	60
13	Flexible graphene field effect transistor with ferroelectric polymer gate. <i>Optical and Quantum Electronics</i> , 2016 , 48, 1	2.4	14
12	Size Effect on Optical and Photocatalytic Properties in BiFeO ₃ Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 3595-3601	3.8	93
11	Ferroelectric control of magnetism in P(VDF-TrFE)/Co heterostructure. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 7502-7506	2.1	9
10	Confinement effect on coercive field in relaxor terpolymer nanowires. <i>Applied Surface Science</i> , 2015 , 355, 473-476	6.7	
9	High temperature coefficient of resistance for a ferroelectric tunnel junction. <i>Applied Physics Letters</i> , 2015 , 107, 062904	3.4	3
8	Space-charge Effect on Electroresistance in Metal-Ferroelectric-Metal capacitors. <i>Scientific Reports</i> , 2015 , 5, 18297	4.9	21
7	Self-polarization in ultrathin Langmuir-Blodgett polymer films. <i>Thin Solid Films</i> , 2014 , 551, 171-173	2.2	6
6	Temperature dependence of electronic transport property in ferroelectric polymer films. <i>Applied Surface Science</i> , 2014 , 316, 497-500	6.7	7
5	Enhanced ferroelectric and dielectric properties of the P(VDF-TrFE)/Ag nanoparticles composite thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2014 , 25, 3461-3465	2.1	9
4	Enhanced piezoelectric response in the artificial ferroelectric polymer multilayers. <i>Applied Physics Letters</i> , 2014 , 105, 222907	3.4	8
3	The intermediate temperature T* revealed in relaxor polymers. <i>Applied Physics Letters</i> , 2014 , 104, 222907	3.4	4
2	Transition of the polarization switching from extrinsic to intrinsic in the ultrathin polyvinylidene fluoride homopolymer films. <i>Applied Physics Letters</i> , 2014 , 104, 182907	3.4	37
1	Fully Light-Modulated Organic Artificial Synapse with the Assistance of Ferroelectric Polarization. <i>Advanced Electronic Materials</i> , 2014 , 2, 101402	6.4	3